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Docket No. SUN-DA-114T
Serial No. 10/743,113In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A semiconductor device, comprising:

a capacitor having a bottom electrode, a dielectric layer and an upper electrode, formed on a semiconductor substrate;

a first insulating layer formed on the semiconductor substrate to cover the capacitor;

a plurality of first contact plugs formed in a plurality of first via holes of the first insulating layer, each of the plurality of first contact plugs being electrically connected to either the bottom or the upper electrodes;

a first metal wiring formed on the first insulating layer and connected to the bottom electrode through one of the first contact plugs;

~~a second insulating layer formed on the first insulating layer;~~

a second contact plug ~~in the second insulating layer~~ formed on the first insulating layer and connected to the upper electrode through another one of the first contact plugs;

~~a second insulating layer formed on the first insulating layer to cover the first metal wiring and the second contact plug;~~

an anti-fuse formed in certain thickness in a second via hole of the second insulating layer and electrically connected to the second contact plug;

a third contact plug filling the second via hole ~~and formed on within the anti-fuse, wherein the third contact plug does not directly contact the second insulating layer;~~ and

a second metal wiring formed on the second insulating layer and electrically connected to the third contact plug ~~and the anti-fuse.~~

2. (Original) The semiconductor device of claim 1, wherein the first and second metal wirings are arranged perpendicular to each other.

3. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

forming capacitors having a bottom electrode, a dielectric layer and an upper electrode on a semiconductor substrate;

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forming a first insulating layer on the semiconductor substrate to cover the capacitors;
forming a plurality of first via holes exposing surfaces of the bottom and upper electrodes by selectively patterning the first insulating layer;
forming a plurality of first contact plugs by filling the first via holes with metal materials;
forming first metal wiring connected to the bottom electrodes through some of the first contact plugs and second contact plugs connected to the upper electrodes through the other first contact plugs, on the first insulating layer;
forming a second insulating layer on the first insulating layer ~~to cover the first metal wiring~~ and the second contact plugs;
forming a plurality of second via holes exposing surfaces of the second contact plugs by selectively patterning the second insulating layer;
successively depositing first and second metal layers on the second insulating layer including the second via holes;
forming anti-fuses and ~~third contact plugs in the second via holes and third contact plugs~~ within the anti-fuses by planarizing the first and second metal layers with the second insulating layer;
and
forming second metal wiring electrically connected to the anti-fuses and the third contact plugs, on the second insulating layer.